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KOREAN PATENT ABSTRACTS

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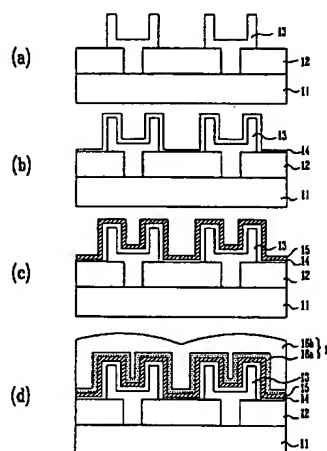
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(54) METHOD FOR MANUFACTURING CAPACITOR OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: A method for manufacturing a capacitor of a semiconductor device is provided to guarantee sufficient capacitance while obtaining an excellent electrical characteristic, by improving a deposition process for forming a Ta₂O₅ thin film used as a dielectric layer of the capacitor to make a thin film having a large dielectric constant and a stable structure.

CONSTITUTION: A lower electrode(13) is formed on a substrate(11) having various elements for forming a semiconductor device. An amorphous (Ta₂O₅)_{1-x}-(TiO₂)_x dielectric layer(15) is formed on the lower electrode. An upper electrode(16) is formed on the (Ta₂O₅)_{1-x}-(TiO₂)_x dielectric layer.



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